

ABSTRACT OF THE DISCLOSURE

Within a method for fabricating a semiconductor integrated circuit microelectronic fabrication there is first provided a first semiconductor substrate. There is then formed over the first semiconductor substrate at least one microelectronic device to form from the first semiconductor substrate a partially fabricated semiconductor integrated circuit microelectronic fabrication. Within the method there is also provided a second substrate. There is also formed over the second substrate, in inverted order, a dielectric isolated metallization pattern intended to mate with the partially fabricated semiconductor integrated circuit microelectronic fabrication. Finally, there is then laminated the partially fabricated semiconductor integrated circuit microelectronic fabrication with the second substrate to mate the partially fabricated semiconductor integrated circuit microelectronic fabrication with the dielectric isolated metallization pattern to thus form a laminated completely fabricated semiconductor integrated circuit microelectronic fabrication. The method provides for enhanced efficiency when fabricating semiconductor integrated circuit microelectronic fabrications.